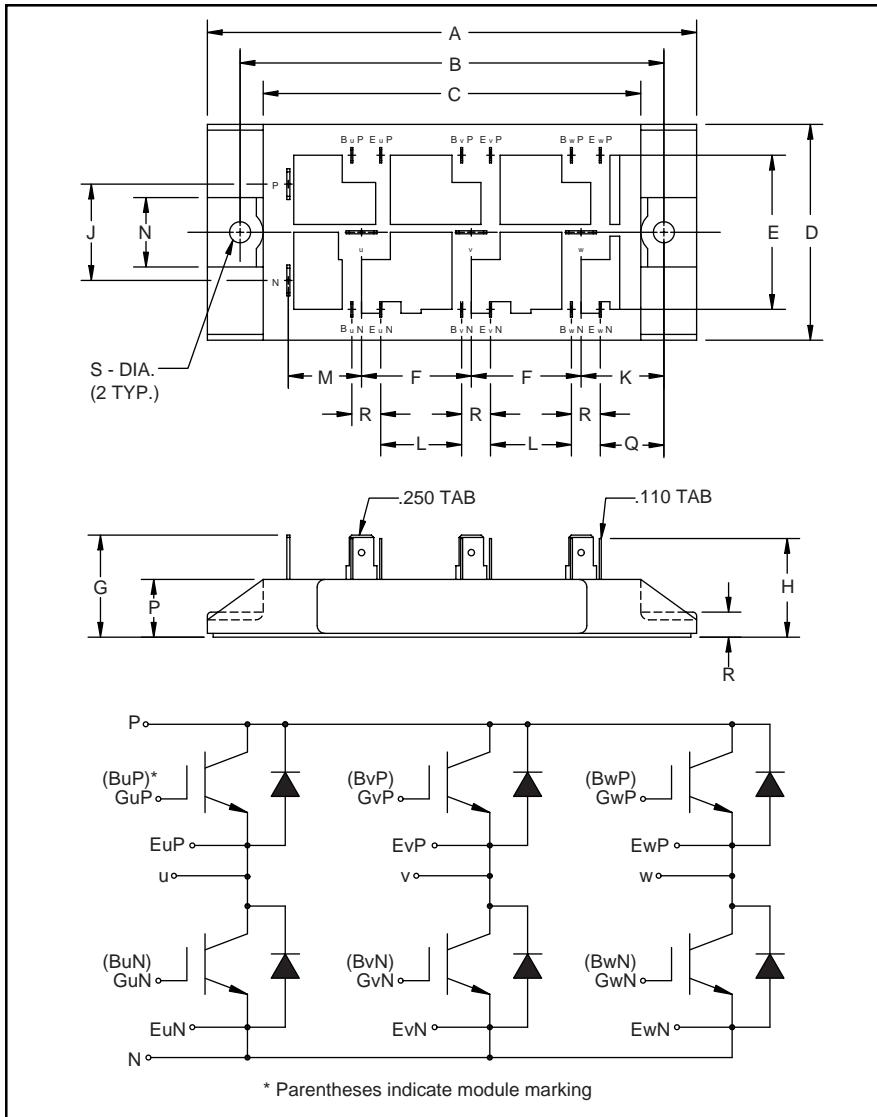


**Six-IGBT IGBTMOD™  
H-Series Module  
50 Amperes/600 Volts**



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.00	127.0
B	4.33±0.01	110.0±0.3
C	3.86	98.0
D	2.20	56.0
E	1.57	40.0
F	1.12	28.5
G	1.04	26.5
H	1.01	25.6
J	0.98	25.0

Dimensions	Inches	Millimeters
K	0.85	21.5
L	0.83	21.0
M	0.75	19.0
N	0.71	18.0
P	0.69	17.5
Q	0.65	16.5
R	0.30	7.5
S	0.22 Dia. Dia. 5.5	



### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- High Frequency Operation (20-25kHz)
- Isolated Baseplate for Easy Heat Sinking

### Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM50TF-12H is a 600V ( $V_{CES}$ ), 50 Ampere Six-IGBT IGBTMOD™ Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	50	12



Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

#### CM50TF-12H

Six-IGBT IGBTMOD™ H-Series Module

50 Amperes/600 Volts

#### Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM50TF-12H	Units
Junction Temperature	$T_j$	-40 to 150	°C
Storage Temperature	$T_{stg}$	-40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	600	Volts
Gate-Emitter Voltage	$V_{GES}$	±20	Volts
Collector Current	$I_C$	50	Amperes
Peak Collector Current	$I_{CM}$	100*	Amperes
Diode Forward Current	$I_F$	50	Amperes
Diode Forward Surge Current	$I_{FM}$	100*	Amperes
Power Dissipation	$P_d$	250	Watts
Max. Mounting Torque M5 Mounting Screws	—	17	in-lb
Module Weight (Typical)	—	390	Grams
V Isolation	$V_{RMS}$	2500	Volts

\* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating.

#### Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 5\text{mA}, V_{CE} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{A}, V_{GE} = 15\text{V}$	—	2.1	2.8**	Volts
		$I_C = 50\text{A}, V_{GE} = 15\text{V}, T_j = 150^\circ\text{C}$	—	2.15	—	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 300\text{V}, I_C = 50\text{A}, V_{GS} = 15\text{V}$	—	150	—	nC
Diode Forward Voltage	$V_{FM}$	$I_E = 50\text{A}, V_{GS} = 0\text{V}$	—	—	2.8	Volts

\*\* Pulse width and repetition rate should be such that device junction temperature rise is negligible.

#### Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$	—	—	5	nF	
Output Capacitance	$C_{oes}$	$V_{GE} = 0\text{V}, V_{CE} = 10\text{V}, f = 1\text{MHz}$	—	—	1.8	nF
Reverse Transfer Capacitance	$C_{res}$	—	—	1	nF	
Resistive	Turn-on Delay Time	$t_{d(on)}$	—	—	200	ns
Load	Rise Time	$t_r$	$V_{CC} = 300\text{V}, I_C = 50\text{A},$	—	300	ns
Switching	Turn-off Delay Time	$t_{d(off)}$	$V_{GE1} = V_{GE2} = 15\text{V}, R_G = 13\Omega$	—	200	ns
Times	Fall Time	$t_f$	—	—	300	ns
Diode Reverse Recovery Time	$t_{rr}$	$I_E = 50\text{A}, di_E/dt = -100\text{A}/\mu\text{s}$	—	—	110	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_E = 50\text{A}, di_E/dt = -100\text{A}/\mu\text{s}$	—	0.14	—	μC

#### Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.50	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDI	—	—	1.00	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	—	—	0.042	°C/W